	Application No.	Applicant(s)	
Nation of Allowability	10/800,348	YAMASHITA, TENKO	
Notice of Allowability	Examiner	Art Unit	
	Theresa T. Doan	2814	
The MAILING DATE of this communication apperature All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in this apport or other appropriate communication GHTS. This application is subject to	plication. If not included will be mailed in due course. <b>THIS</b>	tive
1. $\boxtimes$ This communication is responsive to <u>04/01/05</u> .	•		
2. X The allowed claim(s) is/are 1-16.			
3. $\boxtimes$ The drawings filed on <u>02 August 2004</u> are accepted by the	Examiner.		
<ul> <li>4. Acknowledgment is made of a claim for foreign priority una)</li> <li>a) All b) Some* c) None of the:</li> <li>1. Certified copies of the priority documents have</li> <li>2. Certified copies of the priority documents have</li> <li>3. Copies of the certified copies of the priority documents have</li> <li>International Bureau (PCT Rule 17.2(a)).</li> <li>* Certified copies not received:</li> </ul>	been received. been received in Application No		
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		complying with the requirements	
5. A SUBSTITUTE OATH OR DECLARATION must be subm INFORMAL PATENT APPLICATION (PTO-152) which give	itted. Note the attached EXAMINER es reason(s) why the oath or declara	'S AMENDMENT or NOTICE OF tion is deficient.	
6. CORRECTED DRAWINGS ( as "replacement sheets") mus	t be submitted.		
(a) including changes required by the Notice of Draftspers	on's Patent Drawing Review (PTO-	948) attached	
1) 🔲 hereto or 2) 🔲 to Paper No./Mail Date			
(b) including changes required by the attached Examiner's Paper No./Mail Date	s Amendment / Comment or in the C	Office action of	
Identifying indicia such as the application number (see 37 CFR 1, each sheet. Replacement sheet(s) should be labeled as such in t			
DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT	sit of BIOLOGICAL MATERIAL r	nust be submitted. Note the	
<ul> <li>Attachment(s)</li> <li>1. ☑ Notice of References Cited (PTO-892)</li> <li>2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948)</li> <li>3. ☑ Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date 3/12/04 &amp; 8/10/04</li> <li>4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material</li> </ul>	6. ☐ Interview Summary Paper No./Mail Dat 8), 7. ☑ Examiner's Amendr		

1. Applicant's election of Group I claims 1-16 in the reply filed on 04/01/05 is acknowledged. Because applicant did not distinctly and specifically point out the supposed errors in the restriction requirement, the election has been treated as an election without traverse (MPEP § 818.03(a)).

## **EXAMINER'S AMENDMENT**

2. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

This application is in condition for allowance except for the presence of claims 17-19 non-elected without traverse. Accordingly, claims 17-19 have been cancelled.

## Reasons for Allowance

- 3. Claims 1-16 are allowed.
- 4. The following is an examiner's statement of reasons for allowance:

The prior art of record fails to disclose the combination of a method of forming a semiconductor on insulator (SOI) substrate having at least two exposed surface crystal orientations recited in the base claims 1 and 8. Specifically, the combination of the

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process comprising a step of providing an SOI substrate having a first silicon layer with a surface having a first crystal orientation located on a first buried oxide layer, the buried oxide layer being located on a silicon substrate having a surface with a second crystal orientation; selectively removing the first silicon layer and the fist buried oxide layer to expose a first surface portion of the silicon substrate; epitaxially growing a second silicon layer over the first surface portion of the silicon substrate, the second silicon layer having a surface with a second crystal orientation; and forming a second buried oxide layer in the second silicon layer.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Theresa T. Doan whose telephone number is (571) 272-1704. The examiner can normally be reached on Monday to Friday from 7:00AM - 4:00PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, WAEL FAHMY can be reached on (571) 272-1705. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

TD May 2, 2005.

PHAT X. CAO PRIMARY EXAMINER